

Enhancement Mode Field Effect Transistor

N-Channel

2N7002W

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- These Devices are Pb-Free and are RoHS Compliant

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage $R_{GS} \le 1.0 \text{ M}\Omega$	V_{DGR}	60	V
Gate-Source Voltage Continuous Pulsed	V _{GSS}	±20 ±40	٧
Gate-Source Voltage Continuous Continuous @ 100°C Pulsed	Ι _D	115 73 800	mA
Junction and Storage Temperature Range	T _J , T _{STG}	–55 to +150	°C

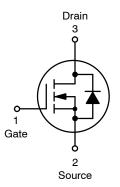
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Total Device Dissipation Derating above T _A = 25°C	P _D	200 1.6	MW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ heta JA}$	625	°C/W

^{1.} Device mounted on FR–4 PCB, 1 inch \times 0.85 inch \times 0.062 inch. Minimum land pad size.

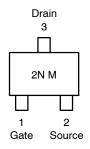
SIMPLIFIED SCHEMATIC





SC-70 CASE 419AB

MARKING DIAGRAM & PIN ASSIGNMENT



2N = Device Code M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
2N7002W	SC-70 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Тур	Max	Units
OFF CHARACTERISTICS (Note 2)	<u></u>						1
Drain-Source Breakdown Voltage	BV _{DSS}	$V_{GS} = 0 \text{ V}, I_D = 10 \mu\text{A}$		60	78	-	V
Zero Gate Voltage Drain Current	I _{DSS}			-	0.001	1.0	μΑ
		V _{DS} = 60 V	T _C = 125°C	-	7	500	1
Gate-Body Leakage Current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{I}$	_{DS} = 0 V	-	0.2	±10	nA
ON CHARACTERISTICS (Note 2)	•						
Gate Threshold Voltage	V _{GS(th)}	$V_{GS} = V_{DS}, I_D = 250 \mu A$		1.0	1.76	2.0	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = 5 V, I _D = 0.05 A		-	1.6	7.5	Ω
		V _{GS} = 10 V, I _D =	= 0.5 A, @ T _J = 125°C	-	2.53	13.5	
On-State Drain Current	I _{D(ON)}	V _{GS} = 10 V, V _{DS} = 7.5 V		0.5	1.43	-	Α
Forward Transconductance	9FS	V _{DS} = 10 V, I _D = 0.2 A		80	356.5	-	mS
DYNAMIC CHARACTERISTICS							
Input Capacitance	C _{ISS}	$V_{GS} = 0 \text{ V}, V_{DS}$	V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz		37.8	50	pF
Output Capacitance	C _{OSS}			-	12.4	25	
Reverse Transfer Capacitance	C _{RSS}			-	6.5	7.0	
SWITCHING CHARACTERISTICS	•				-		-
Turn-On Delay Time	t _{D(ON)}	$V_{GEN} = 10 \text{ V}, V_{DD} = 30 \text{ V}, I_{D} = 0.2 \text{ A},$ $R_{L} = 150 \Omega, R_{GEN} = 25 \Omega$		-	5.85	20	ns
Turn-Off Delay Time	t _{D(OFF)}			_	12.5	20	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Short duration test pulse used to minimize self–heating effect.

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TYPICAL PERFORMANCE CHARACTERISTICS

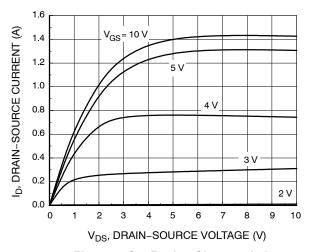


Figure 1. On-Region Characteristics

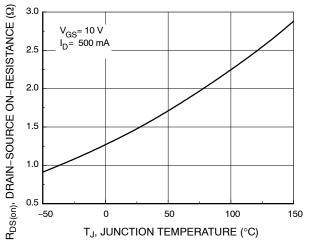


Figure 3. On–Resistance Variation with Temperature

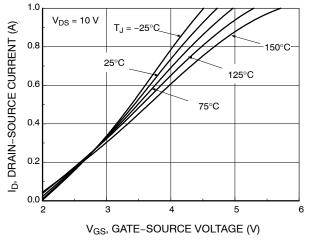


Figure 5. Transfer Characteristics

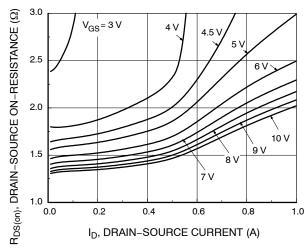


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

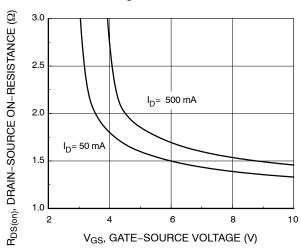


Figure 4. On–Resistance Variation with Gate–Source Voltage

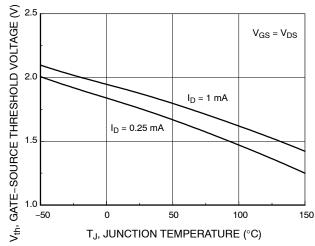


Figure 6. Gate Threshold Variation with Temperature

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TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

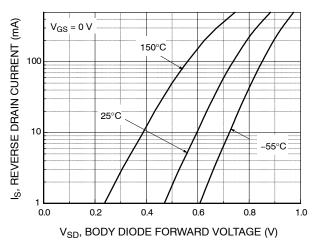


Figure 7. Reverse Drain Current Variation with Diode Forward Voltage and Temperature

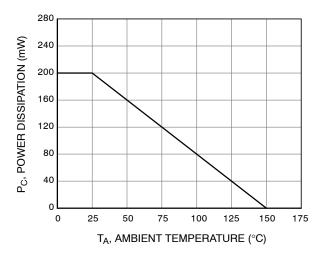
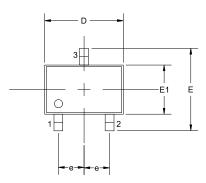


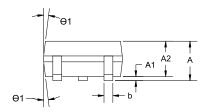
Figure 8. Power Derating



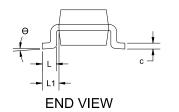




TOP VIEW



SIDE VIEW



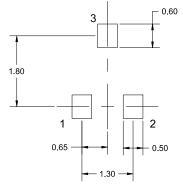
SC-70, 3 Lead, 1.25x2 CASE 419AB ISSUE A

DATE 13 FEB 2023

NOTES:

- 1. ALL DIMENSIONS ARE IN MILLIMETERS. ANGLES IN DEGREES.
- 2. COMPLIES WITH JEDEC MO-203

	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
Α	0.80		1.10
A1	0.00		0.10
A2	0.80	0.90	1.00
b	0.15		0.30
С	0.08		0.22
D	1.80	2.00	2.20
E	1.80	2.10	2.40
E1	1.15	1.25	1.35
е	0.65 BSC		
L	0.26	0.36	0.46
L1	0.42 REF		
θ	0°		8°
Θ1	40		10°



SOLDERING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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